**Product data sheet** 

## 1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a leadless medium power DFN2020MD-6 (SOT1220) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

### 2. Features and benefits

- Extended temperature range T<sub>i</sub> = 175 °C
- Small and leadless ultra thin SMD plastic package: 2 x 2 x 0.65 mm
- Tin-plated 100 % solderable side pads for optical solder inspection
- ElectroStatic Discharge (ESD) protection > 2 kV HBM
- Trench MOSFET technology

## 3. Applications

- · Relay driver
- High-speed line driver
- · Low-side load switch
- · Switching circuits

### 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	30	V
$V_{GS}$	gate-source voltage			-20	-	20	V
I <sub>D</sub>	drain current	$V_{GS} = 10 \text{ V}; T_{amb} = 25 \text{ °C}; t \le 5 \text{ s}$	[1]	-	-	10	Α
Static characteristics							
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = 10 V; $I_D$ = 7.2 A; $T_j$ = 25 °C		-	17	24	mΩ

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.



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# **5. Pinning information**

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	D	drain	1 1 1 1 6	D
2	D	drain		
3	G	gate	2 5	G ← ↓ ‡ ★ \
4	S	source	3 8 4	
5	D	drain	Transparent top view	
6	D	drain	DFN2020MD-6 (SOT1220)	S
7	D	drain		017aaa255
8	S	source		

# 6. Ordering information

**Table 3. Ordering information** 

Type number	Package	е					
	Name	Description	Version				
PMPB25ENE	DFN2020MD-6	DFN2020MD-6: plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals	SOT1220				

# 7. Marking

#### **Table 4. Marking codes**

Type number	Marking code
PMPB25ENE	3V

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# 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> = 25 °C		-	30	V
$V_{GS}$	gate-source voltage			-20	20	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C; t ≤ 5 s	[1]	-	10	А
		V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C	[1]	-	7.2	Α
		V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 100 °C	[1]	-	4.6	А
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \mu s$		-	29	А
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[1]	-	2.1	W
		T <sub>amb</sub> = 25 °C; t ≤ 5 s	[1]	-	4.1	W
		T <sub>sp</sub> = 25 °C		-	12.5	W
Tj	junction temperature			-55	175	°C
T <sub>amb</sub>	ambient temperature			-55	175	°C
T <sub>stg</sub>	storage temperature			-65	175	°C
Source-drain	n diode					
I <sub>S</sub>	source current	T <sub>amb</sub> = 25 °C	[1]	-	2.1	Α

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.

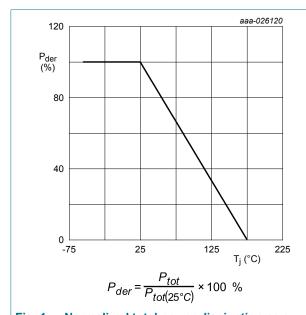


Fig. 1. Normalized total power dissipation as a function of junction temperature

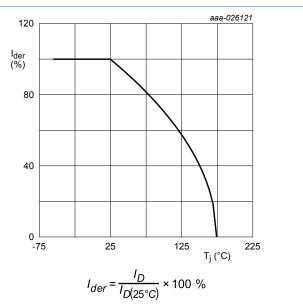


Fig. 2. Normalized continuous drain current as a function of junction temperature

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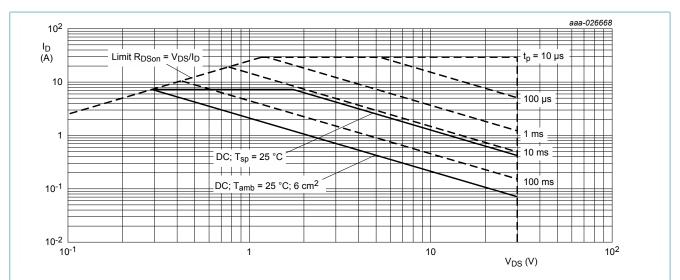


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

30 V, N-channel Trench MOSFET

### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
ung a)	thermal resistance from junction to ambient	in free air	[1]	-	231	265	K/W
			[2]	-	63	72	K/W
		in free air; t ≤ 5 s	[2]	-	32	37	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	9	12	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm<sup>2</sup>.

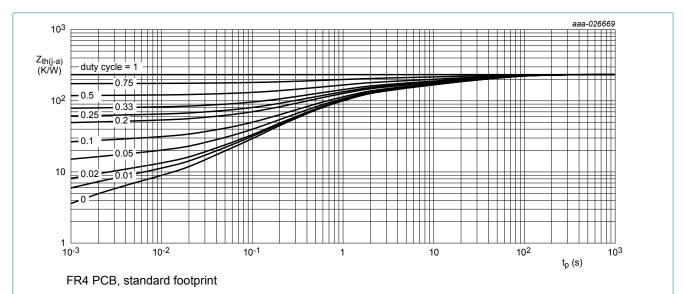


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

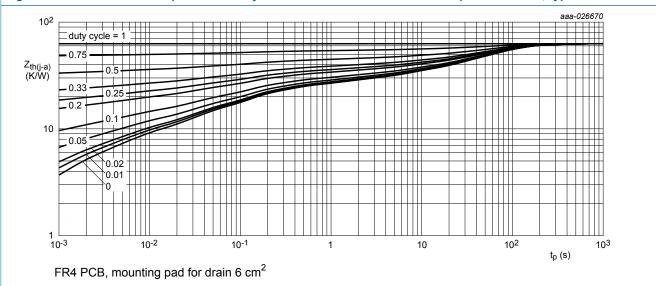


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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### 10. Characteristics

#### Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics				_	
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	30	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D$ = 250 $\mu$ A; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 25 °C	1	1.5	2.5	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 30 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1	μΑ
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	10	μΑ
		V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-10	μΑ
		V <sub>GS</sub> = 4.5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	200	nA
		V <sub>GS</sub> = -4.5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-200	nA
DOUL	drain-source on-state	$V_{GS}$ = 10 V; $I_{D}$ = 7.2 A; $T_{j}$ = 25 °C	-	17	24	mΩ
	resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 7.2 A; T <sub>j</sub> = 175 °C	-	28	40	mΩ
		V <sub>GS</sub> = 4.5 V; I <sub>D</sub> = 6.2 A; T <sub>j</sub> = 25 °C	-	28	32	mΩ
9 <sub>fs</sub>	forward transconductance	$V_{DS}$ = 10 V; $I_D$ = 7.2 A; $T_j$ = 25 °C	-	25	-	S
R <sub>G</sub>	gate resistance	f = 1 MHz	-	6.8	-	Ω
Dynamic ch	naracteristics			<u>'</u>		
Q <sub>G(tot)</sub>	total gate charge	V <sub>DS</sub> = 15 V; I <sub>D</sub> = 7 A; V <sub>GS</sub> = 10 V;	-	13	19	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C	-	1.5	-	nC
Q <sub>GD</sub>	gate-drain charge		-	2.8	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 15 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	607	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	113	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	88	-	pF
t <sub>d(on)</sub>	turn-on delay time	V <sub>DS</sub> = 15 V; I <sub>D</sub> = 7 A; V <sub>GS</sub> = 10 V;	-	6	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	29	-	ns
t <sub>d(off)</sub>	turn-off delay time	_	-	28	-	ns
t <sub>f</sub>	fall time	_	-	12	-	ns
Source-dra	in diode		,			
$V_{SD}$	source-drain voltage	I <sub>S</sub> = 2.1 A; V <sub>GS</sub> = 0 V; T <sub>i</sub> = 25 °C	-	0.8	1.2	V

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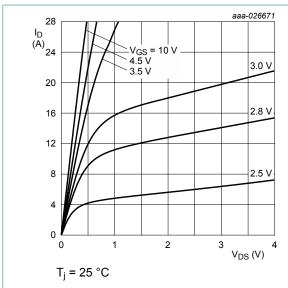


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

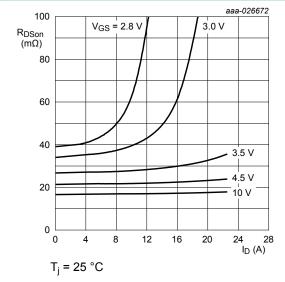


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

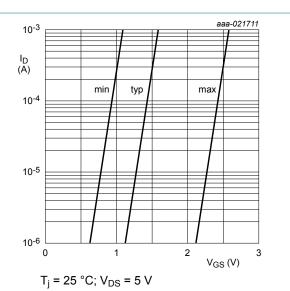


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

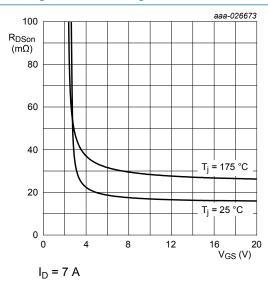


Fig. 9. Drain-source on-state resistance as a function of drain current; typical values

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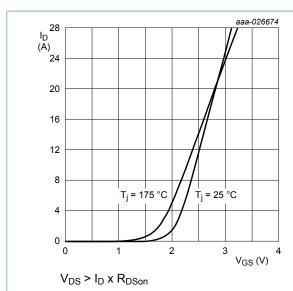


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

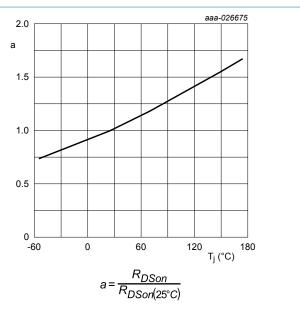


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

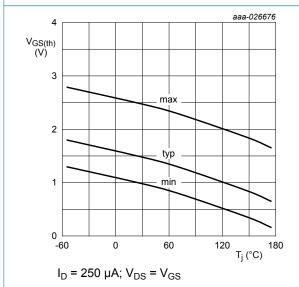


Fig. 12. Gate-source threshold voltage as a function of junction temperature

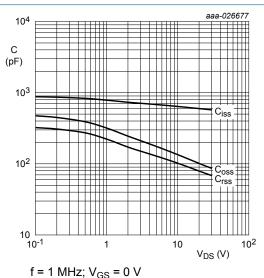


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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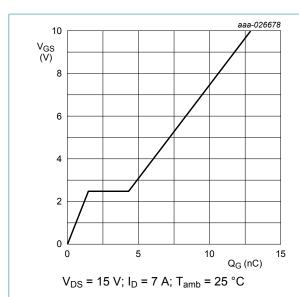


Fig. 14. Gate-source voltage as a function of gate charge; typical values

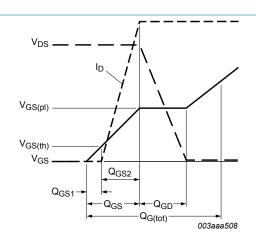


Fig. 15. Gate charge waveform definitions

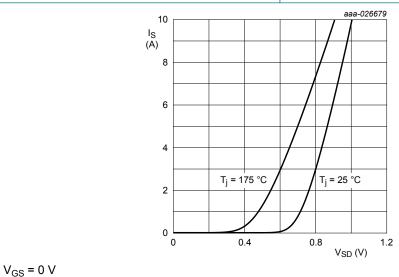
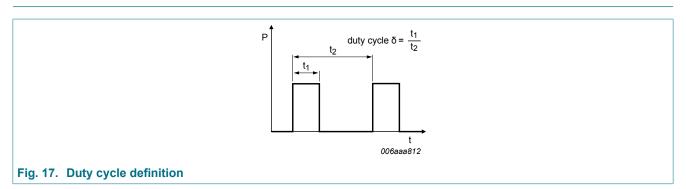


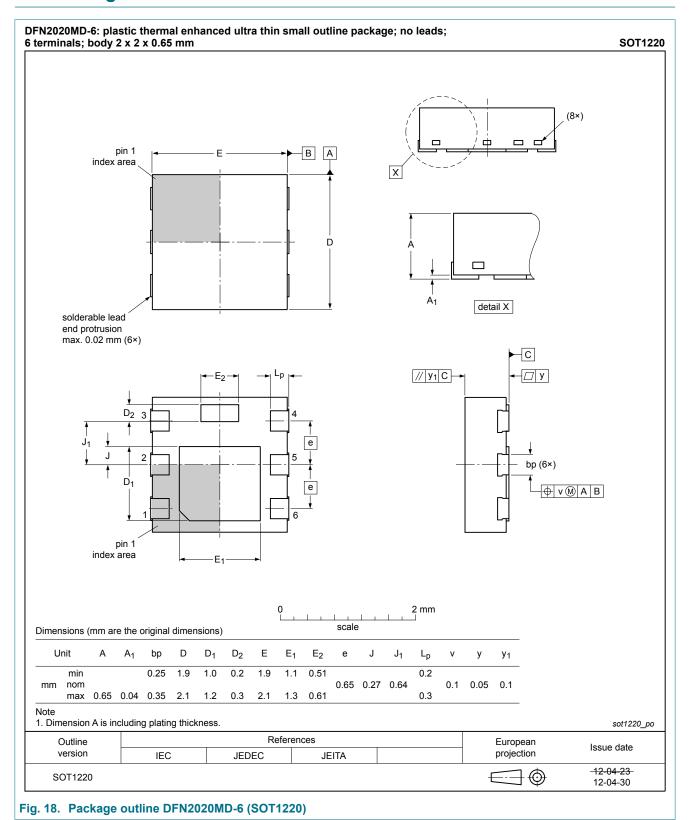
Fig. 16. Source current as a function of source-drain voltage; typical values

### 11. Test information



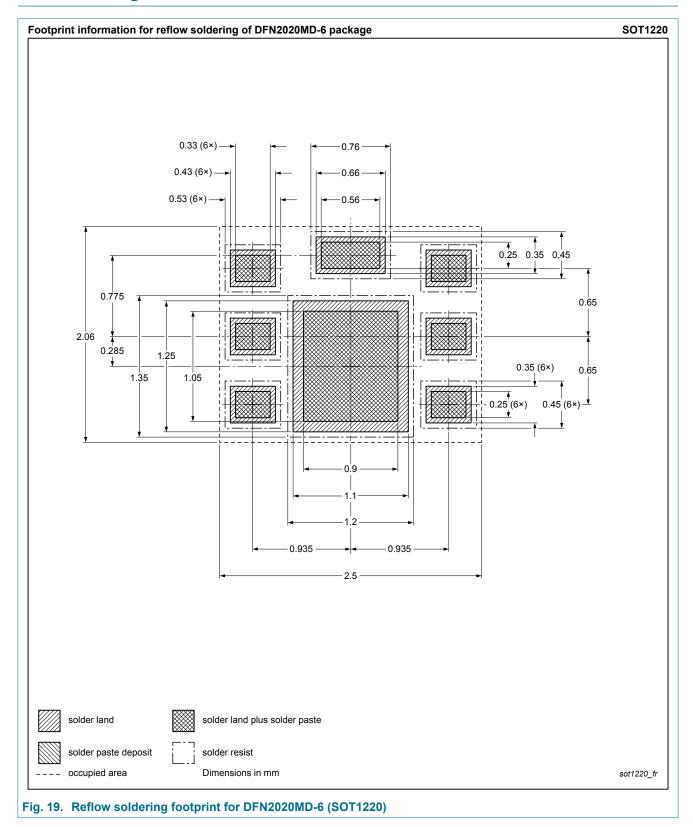
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# 12. Package outline



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# 13. Soldering



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# 14. Revision history

#### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMPB25ENE v.1	20180426	Product data sheet	-	-

#### 30 V, N-channel Trench MOSFET

# 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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